

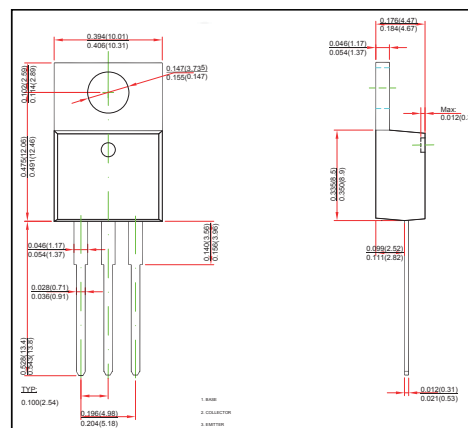
TO-220-3L Plastic-Encapsulate Transistors

FEATURES

- High Current Switching Applications
- Low Collector Saturation Voltage
- High Speed Switching Time
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-220-3Lmolded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-5	A
Collector Power Dissipation	P_C	2	W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -1A$	70		240	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -3A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -150mA$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = -150mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -4V, I_C = -1A$		60		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		170		pF
Turn-on Time	t_{on}	$V_{CC} = -30V, I_C = -3A,$ $I_{B1} = -I_{B2} = -0.15A$		0.1		μs
Storage Time	t_s			1.0		
Fall Time	t_f			0.1		

*Pulse test: $t_0 \leq 300 \mu s$, $\delta \delta \leq 0.02$